

BC856BS

65 V, 100 mA PNP/PNP general-purpose transistor

Rev. 01 — 11 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP general-purpose transistor pair in a very small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package I		NPN/NPN	NPN/PNP
	Nexperia	JEITA	complement	complement
BC856BS	SOT363	SC-88	BC846BS	BC846BPN

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{CEO}	collector-emitter voltage	open base	-	-	-65	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	200	290	450	



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2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	G- G- G-	
2	base TR1	6 5 4	6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	□1 □2 □3	
6	collector TR1		1 2 3
			sym018

3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
BC856BS	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BC856BS	*E6

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

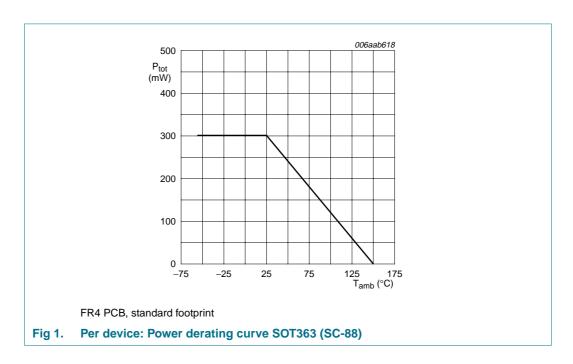
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5. Limiting values

Table 6. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-80	V
V_{CEO}	collector-emitter voltage	open base	-	-65	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u> -	200	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		– 55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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6. Thermal characteristics

Table 7. Thermal characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	625	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	230	K/W
Per device)					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

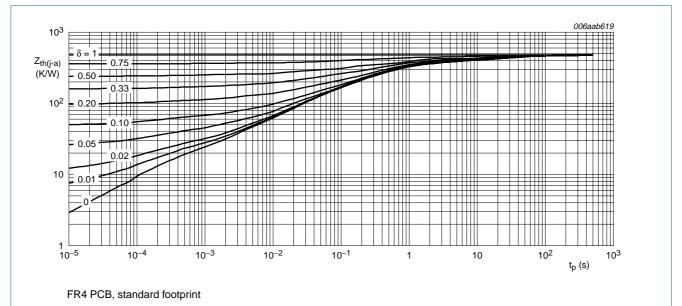


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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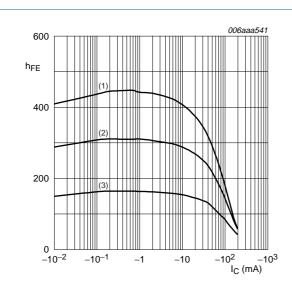
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I _{CBO}		$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-15	nA
	current	$V_{CB} = -30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 \text{ °C}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -6 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}$				
		$I_C = -10 \mu A$	-	270	-	
		$I_C = -2 \text{ mA}$	200	290	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	-	-55	-100	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}$	-	-200	-300	mV
V_{BEsat}	V _{BEsat} base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-755	-850	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}$	-	-900	-	mV
V_{BE}	base-emitter voltage	$V_{CE} = -5 \text{ V}$				
		$I_C = -2 \text{ mA}$	-600	-650	-750	mV
		$I_C = -10 \text{ mA}$	-	-	-820	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	-	2.3	-	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A}; f = 1 \text{ MHz}$	-	10	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
NF noise	noise figure	$V_{CE} = -5 \text{ V}; I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ f = 10 Hz to 15.7 kHz	-	1.6	-	dB
		$V_{CE} = -5 \text{ V}; I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega; f = 1 \text{ kHz};$ B = 200 Hz	-	2.9	-	dB

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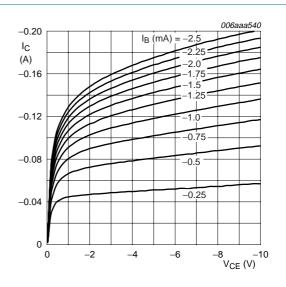
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. Per transistor: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig 4. Per transistor: Collector current as a function of collector-emitter voltage; typical values

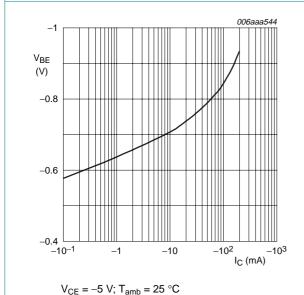
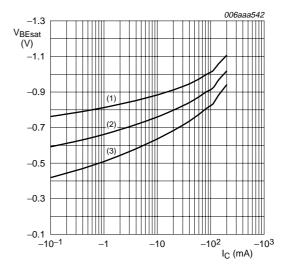


Fig 5. Per transistor: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = -55$$
 °C

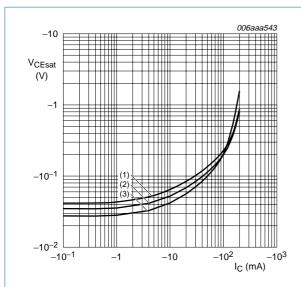
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values

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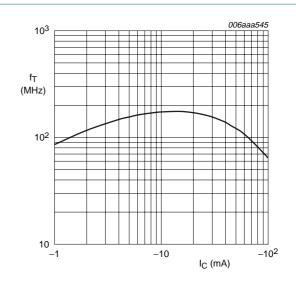
 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

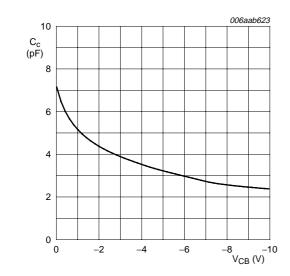
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values



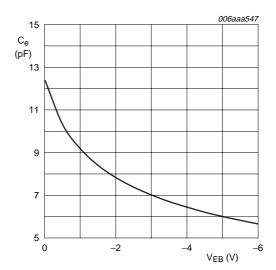
 $V_{CE} = -5 \text{ V}$; $T_{amb} = 25 \, ^{\circ}\text{C}$

Fig 8. Per transistor: Transition frequency as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 9. Per transistor: Collector capacitance as a function of collector-base voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \, ^{\circ}\text{C}$

Fig 10. Per transistor: Emitter capacitance as a function of emitter-base voltage; typical values

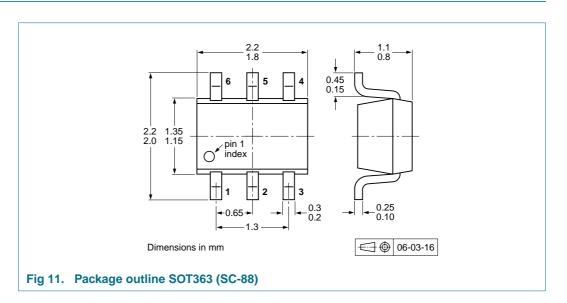
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8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing	acking quantity	
				3000	10000	
BC856BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135	
		4 mm pitch, 8 mm tape and reel; T2	<u>[3]</u>	-125	-165	

^[1] For further information and the availability of packing methods, see $\underline{\text{Section 14}}$.

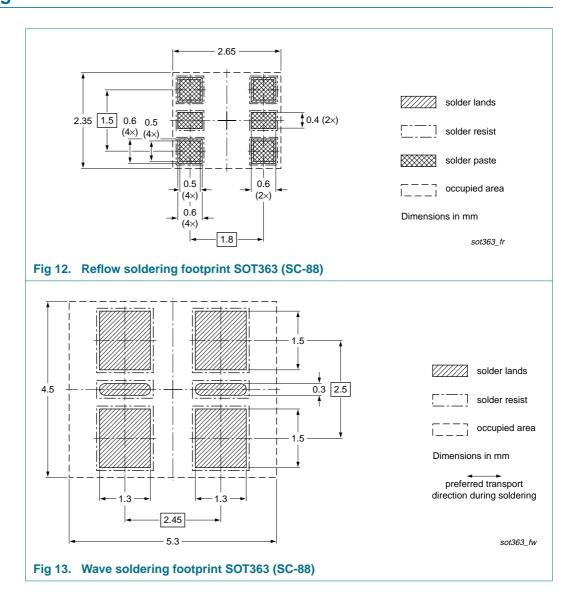
[2] T1: normal taping

[3] T2: reverse taping

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11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC856BS_1	20090811	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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